

RL78/G10

RENESAS MCU

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True Low Power Platform (as low as 46 μ A/MHz), 2.0 to 5.5V Operation, 1 to 4 Kbyte Flash for General Purpose Applications

<R> 1. OUTLINE

1.1 Features

Ultra-Low Power Technology

- 2.0 to 5.5 V operation from a single supply
- Stop (RAM retained): 0.56 μA
- Operating: 46 μA /MHz

RL78-S1 Core

- Instruction execution: 78 % of instructions can be executed in 1 to 2 clock cycles
- CISC architecture (Harvard) with 3-stage pipeline
- Multiply: 8 x 8 to 16-bit result in 2 clock cycles
- 16-bit barrel shifter for shift & rotate in 2 clock cycle
- 1-wire on-chip debug function

Main Flash Memory

- . Density: 1 to 4 Kbyte
- Flash memory rewritable voltage: 4.5 to 5.5 V

RAM

- 128 to 512 Byte size options
- · Supports operands or instructions
- · Back-up retention in all modes

High-speed On-chip Oscillator

- 20 MHz with +/-2 % accuracy over voltage (2.0 to 5.5 V) and temperature (-20 to +85°C)
- Pre-configured settings: 20 MHz, 10 MHz, 5 MHz, 2.5 MHz, and 1.25 MHz

Reset and Supply Management

 Selectable power-on reset (SPOR) generator with 4 setting options

Multiple Communication Interfaces

- 1 x I2C master
- 1 x I²C multi-master (only for 16-pin product)
- 1 x UART (7-, 8-bit)
- Up to 2 x CSI/SPI (7-, 8-bit)

Extended-Function Timers

- Multi-function 16-bit timers: Up to 4 channels
- Interval timer: 12-bit, 1 channel (only for 16-pin product)
- 15 kHz watchdog timer: 1 channel

Rich Analog

- ADC: Up to 7 channels, 10-bit resolution, 3.4 µs conversion time
- Supports 2.4 V
- Internal reference voltage (0.815 V (typ.))
- Comparator: 1 channel (only for 16-pin product)

Safety Features

- Detects execution of illegal instruction
- · Detects watchdog timer program loop

General Purpose I/O

- High-current (up to 20 mA per pin)
- Open-drain, internal pull-up support

External Interrupt

- External interrupt input: Up to 4
- Key interrupt input: 6

Operating Ambient Temperature

• Standard: -40 to +85°C

Package Type and Pin Count

• SSOP: 10 and 16 pin

O ROM, RAM capacities

Flash ROM	RAM	10 pins	16 pins
4 KB	512 B	R5F10Y17ASP Note 2	R5F10Y47ASP Note 2
2 KB	256 B	R5F10Y16ASP	R5F10Y46ASP Note 2
1 KB	128 B	R5F10Y14ASP	R5F10Y44ASP Note 2

Notes 1. 16-pin products only

2. Under development

Remark The functions mounted depend on the product. See **1.6 Outline of Functions**.

<R> 1.2 List of Part Numbers

Figure 1-1. Part Number, Memory Size, and Package of RL78/G10

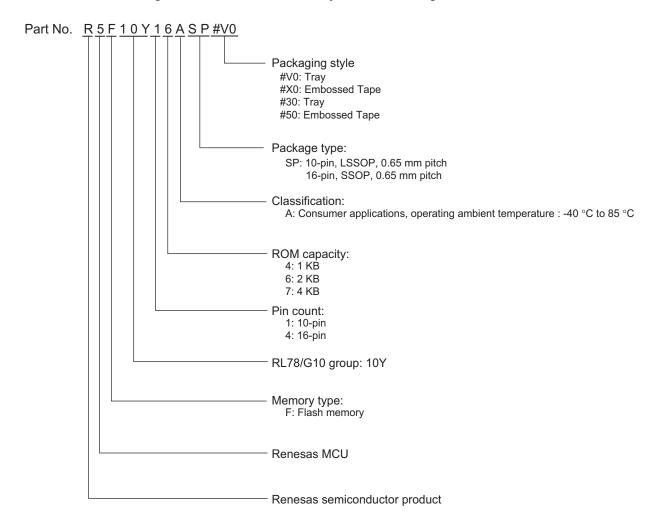


Table 1-1. List of Ordering Part Numbers

Pin count	Package	Part Number
10 pins	10-pin plastic LSSOP	R5F10Y17ASP#30 Note, R5F10Y17ASP#50 Note
	(4.4 × 3.6 mm, 0.65 mm pitch)	R5F10Y16ASP#V0, R5F10Y16ASP#X0
		R5F10Y14ASP#V0, R5F10Y14ASP#X0
16 pins	16-pin plastic SSOP	R5F10Y47ASP#30 Note, R5F10Y47ASP#50 Note
	(4.4 × 5.0 mm, 0.65 mm pitch)	R5F10Y46ASP#30 Note, R5F10Y46ASP#50 Note
		R5F10Y44ASP#30 Note, R5F10Y44ASP#50 Note

Note Under development

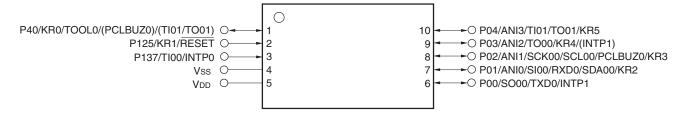
Caution The part number represents the number at the time of publication.

Be sure to review the latest part number through the target product page in the Renesas Electronics Corp.website.

1.3 Pin Configuration (Top View)

1.3.1 10-pin products

• 10-pin plastic LSSOP (4.4 × 3.6 mm, 0.65 mm pitch)

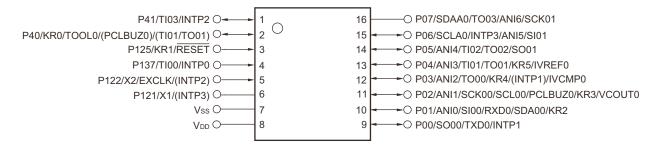


Remarks 1. For pin identification, see 1.4 Pin Identification.

2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). See Figure 4-6 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G10 User's Manual.

1.3.2 16-pin products

• 16-pin plastic SSOP (4.4 × 5.0 mm, 0.65 mm pitch)



- Remarks 1. For pin identification, see 1.4 Pin Identification.
 - 2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). See Figure 4-6 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G10 User's Manual.

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1.4 Pin Identification

ANI0 to ANI6 : Analog Input

INTP0 to INTP3 : External Interrupt Input

KR0 to KR5 : Key Return
P00 to P07 : Port 0
P40, P41 : Port 4
P121, P122, P125 : Port 12
P137 : Port 13

PCLBUZ0 : Programmable Clock Output/ Buzzer Output

EXCLK : External Clock Input
X1, X2 : Crystal Oscillator
IVCMP0 : Comparator Input
VCOUT0 : Comparator Output

IVREF0 : Comparator Reference Input

RESET : Reset

RxD0 : Receive Data

SCK00, SCK01 : Serial Clock Input/Output
SCL00, SCLA0 : Serial Clock Output

SDA00, SDAA0 : Serial Data Input/Output

SI00, SI01 : Serial Data Input SO00, SO01 : Serial Data Output

TI00 to TI03 : Timer Input
TO00 to TO03 : Timer Output

TOOL0 : Data Input/Output for Tool

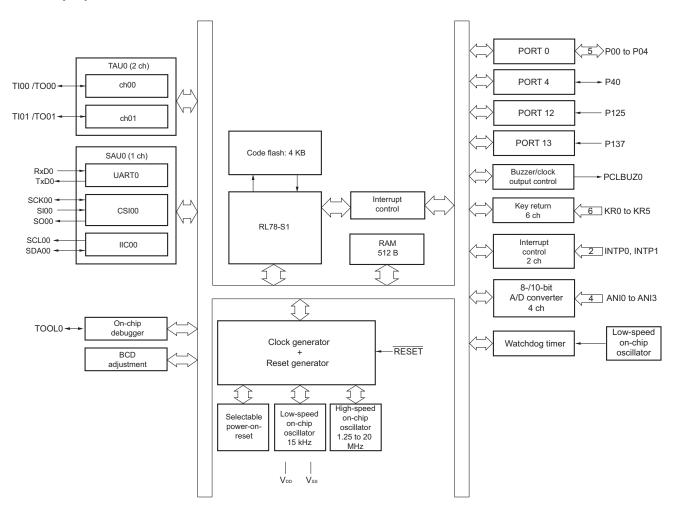
TxD0 : Transmit Data

Vdd : Power Supply

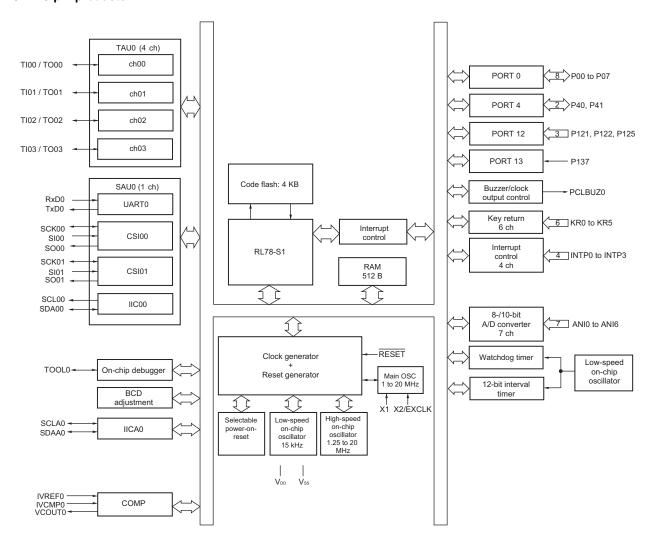
Vss : Ground

1.5 Block Diagram

1.5.1 10-pin products



1.5.2 16-pin products



1.6 Outline of Functions

This outline describes the function at the time when Peripheral I/O redirection register (PIOR) is set to 00H.

	Item		10-pin			16-pin		
		R5F10Y14ASP	R5F10Y16ASP	R5F10Y17ASP	R5F10Y44ASP	R5F10Y46ASP	R5F10Y47AS	
Code flash	memory	1 KB	2 KB	4 KB	1 KB	2 KB	4 KB	
RAM		128 B	256 B	512 B	128 B	256 B	512 B	
Main	High-speed system	-			X1, X2 (crystal	/ceramic) oscillati	on, external	
system	clock					lock input (EXCL	():	
clock		1 to 20 MHz: VDD = 2.7 to 5.5 V						
					1 to 5 MHz: VD	$D = 2.0 \text{ to } 5.5 \text{ V}^{\text{No}}$	ite 3	
	High-speed on-chip		IHz (VDD = 2.7 to	,				
	oscillator clock		Hz (VDD = 2.0 to	5.5 V Note 3)				
Low-speed clock	d on-chip oscillator	15 kHz (TYP)						
General-pu	urpose register	8-bit register ×	: 8					
Minimum i	nstruction execution	0.05 μs (20 M	Hz operation)					
time								
Instruction	set	Data transfe	er (8 bits)					
			-	operation (8 bits	s)			
			n (8 bits \times 8 bits)					
		-	el shift, and bit n	•				
	1	, , ,	est, and Boolear	operation), etc.	T			
I/O port	Total	8			14			
	CMOS I/O		drain output (VDI	tolerance): 2)		-drain output (VDE	tolerance): 4)	
	CMOS input	2			4			
Timer	16-bit timer	2 channels			4 channels			
	Watchdog timer	1 channel			l			
	12-bit interval timer	 -			1 channel	Note	1,	
	Timer output	2 channels (P	WM output: 1)		4 channels (PV	VM outputs: 3 Note	')	
Clock outp	ut/buzzer output	1						
		2.44 kHz to 10) MHz: (Peripher	al hardware cloc	k: fmain = 20 MHz (I .	operation)		
Comparato		 -			1			
	esolution A/D converter	4 channels	. 1 001		7 channels			
Serial inter	Tace		-	•	1 channel/UART:			
	I ² C bus		cisj CSI: 2 chann	ieis/simpilitied i C	: 1 channel/UART	: i channei		
\/aatarad		8			1 channel			
Vectored interrupt	Internal External	3			14 5			
sources	External	3			5			
Key interru	ınt	6			I			
Reset	.ρ.	Reset by RE	SFT nin					
110001		-	et by watchdog t	imer				
			et by selectable i					
				uction execution	Note 2			
				on lower limit vol				
Selectable	power-on-reset circuit	Detection vo						
	,			2.68 V/3.02 V/4.4	5 V (max.)			
				2.62 V/2.96 V/4.3				



Item		10-pin R5F10Y14ASP R5F10Y16ASP Provided VDD = 2.0 to 5.5 V Note 3			16-pin		
	R5F10Y14ASP	R5F10Y16ASP	R5F10Y17ASP	R5F10Y44ASP	R5F10Y46ASP	R5F10Y47ASP	
On-chip debug function	Provided						
Power supply voltage	V _{DD} = 2.0 to 5	5.5 V Note 3					
Operating ambient temperature	Ta = - 40 to +	85 °C					

- Notes 1. The number of outputs varies, depending on the setting of channels in use and the number of the master (see 6.9.4 Operation as multiple PWM output function in the RL78/G10 User's Manual).
 - 2. The illegal instruction is generated when instruction code FFH is executed. Reset by the illegal instruction execution not issued by emulation with the on-chip debug emulator.
 - **3.** Use this product within the voltage range from 2.25 to 5.5 V because the detection voltage (Vspor) of the selectable power-on-reset (SPOR) circuit should also be considered.

2. ELECTRICAL SPECIFICATIONS

- Cautions 1. The RL78 microcontrollers have an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.
 - 2. The pins mounted depend on the product. Refer to 2.1 Port Functions and 2.2.1 Functions for each product in the RL78/G10 User's Manual.
 - 3. Use this product within the voltage range from 2.25 to 5.5 V because the detection voltage (Vspor) of the selectable power-on-reset (SPOR) circuit should also be considered.

<R>> 2.1 Absolute Maximum Ratings

 $(T_A = 25^{\circ}C)$

Parameter	Symbols	Co	onditions	Ratings	Unit
Supply Voltage	V _{DD}			-0.5 to +6.5	V
Input Voltage	Vıı			-0.3 to V _{DD} + 0.3 ^{Note}	V
Output Voltage	V _{O1}			-0.3 to V _{DD} + 0.3	V
Output current, high	Іон1	Per pin		-40	mA
		Total of all pins	P40, P41	-70	mA
		P00 to P07		-100	mA
Output current, low	I _{OL1}	Per pin	•	40	mA
		Total of all pins	P40, P41	70	mA
			P00 to P07	100	mA
Operating ambient temperature	Та			-40 to +85	°C
Storage temperature	T _{stg}			-65 to +150	°C

Note Must be 6.5 V or lower.

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

Remarks 1. Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

2. The reference voltage is Vss.

<R> 2.2 Oscillator Characteristics

2.2.1 X1 oscillator characteristics

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.0 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Resonator	Conditions	MIN.	TYP.	MAX.	Unit
X1 clock	Ceramic resonator/	$2.7~V \leq V_{DD} \leq 5.5~V$	1		20	MHz
oscillation frequency (fx) ^{Note}	crystal resonator	$2.0~\textrm{V} \leq \textrm{V}_\textrm{DD} < 2.7~\textrm{V}$	1		5	MHz

Note Indicates only permissible oscillator frequency ranges. Refer to AC Characteristics for instruction execution time. Request evaluation by the manufacturer of the oscillator circuit mounted on a board to check the oscillator characteristics.

Caution Since the CPU is started by the high-speed on-chip oscillator clock after a reset release, check the X1 clock oscillation stabilization time using the oscillation stabilization time counter status register (OSTC) by the user. Determine the oscillation stabilization time of the OSTC register and the oscillation stabilization time select register (OSTS) after sufficiently evaluating the oscillation stabilization time with the resonator to be used.

Remark When using the X1 oscillator, refer to 5.4 System Clock Oscillator in the RL78/G10 User's Manual.

2.2.2 On-chip oscillator characteristics

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.0 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Oscillators	Parameters	Conditions	MIN.	TYP.	MAX.	Unit
High-speed on-chip oscillator oscillation clock frequency Notes 1, 2	fін		1.25		20	MHz
High-speed on-chip oscillator oscillation		Ta = -20 to +85°C	-2.0		+2.0	%
clock frequency accuracy		Ta = -40 to -20°C	-3.0		+3.0	%
Low-speed on-chip oscillator oscillation clock frequency	fıL			15		kHz
Low-speed on-chip oscillator oscillation clock frequency accuracy			-15		+15	%

Notes 1. High-speed on-chip oscillator frequency is selected by bits 0 to 2 of option byte (000C2H).

2. This only indicates the oscillator characteristics. Refer to AC Characteristics for instruction execution time.

2.3 DC Characteristics

<R> 2.3.1 Pin characteristics

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.0 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

(1/2)

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Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, high	Іон1	Per pin for 10-pin products: P00 to P04, P40 16-pin products: P00 to P07, P40, P41				-10.0 Note 2	mA
		Total of 10-pin products: P40	$4.0 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}$ $2.7 \text{ V} \le \text{V}_{DD} < 4.0 \text{ V}$			-20.0 -4.0	mA mA
		16-pin products: P40, P41 (When duty ≤ 70% ^{Note 3})	$2.0~V \leq V_{DD} < 2.7~V$			-3.0	mA
		Total of	$4.0~V \leq V_{DD} \leq 5.5~V$			-60.0	mA
		10-pin products: P00 to P04	$2.7~V \leq V_{DD} < 4.0~V$			-12.0	mΑ
		16-pin products: P00 to P07 (When duty ≤ 70% Note 3)	$2.0~\textrm{V} \leq \textrm{V}_\textrm{DD} < 2.7~\textrm{V}$			-9.0	mA
		Total of all pins (When duty $\leq 70\%$ Note 3)				-80.0	mΑ
Output current, low	lo _{L1}	Per pin for 10-pin products: P00 to P04, P40 16-pin products: P00 to P07, P40, P41				20.0 Note 2	mA
		Total of	$4.0~V \leq V_{DD} \leq 5.5~V$			40.0	mA
		10-pin products: P40	$2.7~V \leq V_{DD} < 4.0~V$			6.0	mA
		16-pin products: P40, P41 (When duty ≤ 70% Note 3)	$2.0~V \leq V_{DD} < 2.7~V$			1.2	mA
		Total of	$4.0~V \leq V_{DD} \leq 5.5~V$			80.0	mA
		10-pin products: P00 to P04	$2.7~V \leq V_{DD} < 4.0~V$			12.0	mA
		16-pin products: P00 to P07 (When duty ≤ 70% ^{Note 3})	$2.0~V \leq V_{DD} < 2.7~V$			2.4	mA
		Total of all pins (When duty $\leq 70\%$ Note 3)				120.0	mA

Notes 1. Value of current at which the device operation is guaranteed even if the current flows from the V_{DD} pin to an output pin.

- 2. Do not exceed the total current value.
- 3. This is the output current value under conditions where the duty factor $\leq 70\%$.

The output current value when the duty factor > 70% can be calculated with the following expression (when changing the duty factor to n%).

- Total output current of pins = $(IOH \times 0.7)/(n \times 0.01)$
 - <Example> Where n = 80 % and IoH = 10.0 mA

Total output current of pins = $(-10.0 \times 0.7)/(80 \times 0.01) \cong -8.7$ mA

- Total output current of pins = $(lol \times 0.7)/(n \times 0.01)$
 - <Example> Where n = 80 % and lol = 10.0 mA

Total output current of pins = $(10.0 \times 0.7)/(80 \times 0.01) \approx 8.7$ mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

4. Value of current at which the device operation is guaranteed even if the current flows from an output pin to the Vss pin.

Caution P00, P01, P06, and P07 do not output high level in N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port.

(2/2)

 $< R > (TA = -40 \text{ to } +85^{\circ}C, 2.0 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{ Vss} = 0 \text{ V})$

Parameter	Symbol	Condition	IS	MIN.	TYP.	MAX.	Uni
Input voltage, high	V _{IH1}			0.8 V _{DD}		V _{DD}	V
Input voltage, low	V _{IL1}			0		0.2 V _{DD}	V
Output voltage, high	V _{OH1}	$4.0 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}$	Iон = -10 mA	V _{DD} - 1.5			٧
Note 1			Iон = -3.0 mA	V _{DD} - 0.7			V
		$2.7~V \le V_{DD} \le 5.5~V$	Iон = -2.0 mA	V _{DD} - 0.6			٧
		$2.0~V \leq V_{DD} \leq 5.5~V$	Iон = -1.5 mA	V _{DD} - 0.5			٧
Output voltage, low	V _{OL1}	$4.0~V \leq V_{DD} \leq 5.5~V$	IoL = 20 mA			1.3	٧
Note 2			IoL = 8.5 mA			0.7	V
		$2.7~V \leq V_{DD} \leq 5.5~V$	IoL = 3.0 mA			0.6	٧
			IoL = 1.5 mA			0.4	V
		$2.0~V \leq V_{DD} \leq 5.5~V$	IoL = 0.6 mA			0.4	٧
Input leakage	ILIH1	P00 to P07, P40, P41, P125, P137	1			1	μA
current, high		$V_{I} = V_{DD}$					
	I _{LIH2}	P121, P122 (X1, X2, EXCLK)	In input port or			1	
		$V_{I} = V_{DD}$	external clock input				
			In resonator			10	
			connection				
Input leakage	ILIL1	P00 to P07, P40, P41, P125, P137				-1	μA
current, low		Vi = Vss					
	ILIL2	P121, P122 (X1, X2, EXCLK)	In input port or			-1	
		Vı = Vss	external clock input				
			In resonator			-10	
			connection				
On-chip pull-up resistance	R∪	V _I = V _{SS}		10	20	100	kΩ

Notes 1. The value under the condition which satisfies the high-level output current (IOH1).

2. The value under the condition which satisfies the low-level output current (IoL1).

Caution The maximum value of V_{IH} of P00, P01, P06, and P07 is V_{DD} even in N-ch open-drain mode. P00, P01, P06, and P07 do not output high level in N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port.

2.3.2 Supply current characteristics

(1) Flash ROM: 1 and 2 KB of 10-pin products

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.0 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol			Conditions		MIN.	TYP.	MAX.	Unit
Supply current	I _{DD1}	Operating mode	Basic operation	fін = 20 MHz	$V_{DD} = 3.0 \text{ V}, 5.0 \text{ V}$		0.91		mA
			Normal	fін = 20 MHz	$V_{DD} = 3.0 \text{ V}, 5.0 \text{ V}$		1.57	2.04	
			operation	fıн = 5 MHz	$V_{DD} = 3.0 \text{ V}, 5.0 \text{ V}$		0.85	1.15	
	DD2 ^{Note 2}	HALT mode)	fін = 20 MHz	$V_{DD} = 3.0 \text{ V}, 5.0 \text{ V}$		350	820	μΑ
				fıн = 5 MHz	V _{DD} = 3.0 V, 5.0 V		290	600	
	IDD3 ^{Note 3}	STOP mode	е	V _{DD} = 3.0 V			0.56	2.00	μΑ

- **Notes 1.** Total current flowing into V_{DD}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD} or Vss. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, I/O port, and on-chip pull-up/pull-down resistors.
 - 2. During HALT instruction execution by flash memory.
 - 3. Not including the current flowing into the watchdog timer.

Remarks 1. fin: High-speed on-chip oscillator clock frequency

2. Temperature condition of the typical value is $T_A = 25^{\circ}C$

$_{< R>}$ (2) Flash ROM: 4 KB of 10-pin products, and 16-pin products

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.0 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol			Conditions		MIN.	TYP.	MAX.	Unit
Supply current Note 1	I _{DD1}	Operating mode	Basic operation	f _{IH} = 20 MHz Note 4	$V_{DD} = 3.0 \text{ V}, 5.0 \text{ V}$		0.92		mA
			Normal operation	fIH = 20 MHz Note 4	$V_{DD} = 3.0 \text{ V}, 5.0 \text{ V}$		1.59	2.14	
				fIH = 5 MHz Note 4	$V_{DD} = 3.0 \text{ V}, 5.0 \text{ V}$		0.87	1.20	
				fмх = 20 MHz	Square wave input		1.43	1.93	
				Notes 5, 6 VDD = 3.0 V, 5.0 V	Resonator connection		1.54	2.13	
				fmx = 5 MHz	Square wave input		0.67	1.02	
				Notes 5, 6 VDD = 3.0 V, 5.0 V	Resonator connection		0.72	1.12	
	IDD2 Note 2	HALT mode		f _{IH} = 20 MHz Note 4	$V_{DD} = 3.0 \text{ V}, 5.0 \text{ V}$		360	900	μA
				fIH = 5 MHz Note 4	$V_{DD} = 3.0 \text{ V}, 5.0 \text{ V}$		310	660	
				fмх = 20 MHz	Square wave input		200	700	
				Notes 5, 6 VDD = 3.0 V, 5.0 V	Resonator connection		300	900	
				fmx = 5 MHz	Square wave input		100	440	
				Notes 5, 6 VDD = 3.0 V, 5.0 V	Resonator connection		150	540	
	IDD3 ^{Note 3}	STOP mode	9	V _{DD} = 3.0 V			0.61	2.25	μA

- Notes 1. Total current flowing into V_{DD}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD} or V_{SS}. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, comparator (16-pin products only), I/O port, and on-chip pull-up/pull-down resistors.
 - 2. During HALT instruction execution by flash memory.
 - 3. Not including the current flowing into the 12-bit interval timer and watchdog timer.
 - 4. When the high-speed system clock is stopped.
 - **5.** When the high-speed on-chip oscillator is stopped.
 - 6. 16-pin products only

Remarks 1. fin: High-speed on-chip oscillator clock frequency

- 2. fmx: High-speed system clock frequency (X1 clock oscillator frequency or external main system clock frequency)
- **3.** Temperature condition of the typical value is $T_A = 25^{\circ}C$

$_{<\mathsf{R}>}$ (3) Peripheral Functions (Common to all products)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.0 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol		Conditions	MIN.	TYP.	MAX.	Unit
Low-speed on- chip oscillator operating current	Fil Note 1				0.30		μΑ
12-bit interval timer operating current	ITMKA Notes 1, 2, 3				0.01		μΑ
Watchdog timer operating current	WDT Notes 1, 4				0.01		μА
A/D converter	IADC	When conversion	V _{DD} = 5.0 V		1.30	1.90	mA
operating current	Notes 1, 5	at maximum speed	V _{DD} = 3.0 V		0.50		mA
Comparator operating	ICMP Notes 1, 6	In high-speed mode	V _{DD} = 5.0 V		6.50		μА
current		In low-speed mode	V _{DD} = 5.0 V		1.70		μА
Internal reference voltage operating current	IVREG Note 1				10		μА

Notes 1. Current flowing to VDD.

- 2. When high speed on-chip oscillator and high-speed system clock are stopped.
- 3. Current flowing only to the 12-bit interval timer (excluding the operating current of the low-speed on-chip oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either IDD1, IDD2 or IDD3 and IFIL and ITMKA, when the 12-bit interval timer is in operation.
- **4.** Current flowing only to the watchdog timer (excluding the operating current of the low-speed on-chip oscillator). The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and IFIL and IWDT when the watchdog timer is in operation.
- **5.** Current flowing only to the A/D converter. The supply current of the RL78 microcontrollers is the sum of IDD1 or IDD2 and IADC when the A/D converter operates in an operation mode or the HALT mode.
- **6.** Current flowing only to the comparator. The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and ICMP when the comparator is in operation.

Remarks

- 1. fil: Low-speed on-chip oscillator clock frequency
 - 2. Temperature condition of the typical value is $T_A = 25^{\circ}C$

2.4 AC Characteristics

RESET low-level width

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.0 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

$\cdot $	Items	Symbol	Condi	tions	MIN.	TYP.	MAX.	Unit
	Instruction cycle (minimum	Тсү	When high-speed on-	$2.7~V \leq V_{DD} \leq 5.5~V$	0.05		0.8	μs
	instruction execution time)		chip oscillator clock (f _{IH}) is selected	$2.0~\textrm{V} \leq \textrm{V}_\textrm{DD} < 2.7~\textrm{V}$	0.2		0.8	μs
			When high-speed	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$	0.05		1.0	μs
			system clock (f _{MX}) is selected	$2.0~\textrm{V} \leq \textrm{V}_\textrm{DD} < 2.7~\textrm{V}$	0.2		1.0	μs
	External system clock	Tex		$2.7~V \leq V_{DD} \leq 5.5~V$	1.0		20	MH
	frequency			$2.0 \text{ V} \le \text{V}_{DD} < 2.7 \text{ V}$	1.0		5	MH:
	External system clock input	TEXH, TEXL		$2.7~V \leq V_{DD} \leq 5.5~V$	24			ns
	high-level width, low-level width			$2.0~\textrm{V} \leq \textrm{V}_\textrm{DD} < 2.7~\textrm{V}$	95			ns
ı	TI00 to TI03 input high-level width, low-level width	tтін, tті∟	Noise filter is not used		1/fмск + 10			ns
	TO00 to TO03 output	fто	$4.0~V \leq V_{DD} \leq 5.5~V$				10	MH
	frequency		$2.7~V \leq V_{DD} < 4.0~V$				5	MH
			$2.0~V \leq V_{DD} < 2.7~V$				2.5	MH
	PCLBUZ0 output frequency	fpcL	$4.0~V \leq V_{DD} \leq 5.5~V$				10	MH
			$2.7~V \leq V_{DD} < 4.0~V$				5	MH:
ĺ			20 V < Vpp < 2.7 V				2.5	МН

Remark fmck: Timer array unit operation clock frequency

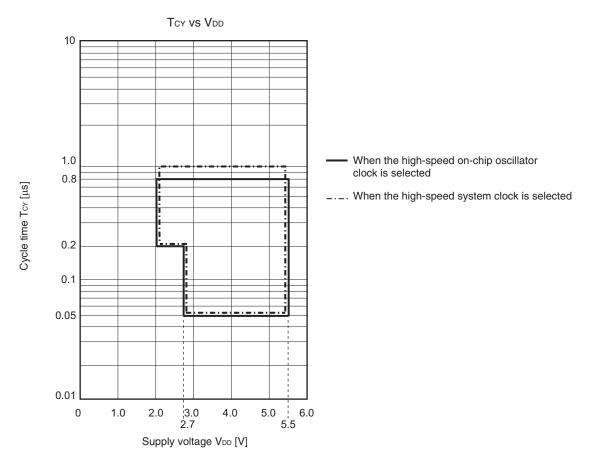
trsL

(Operation clock to be set by the timer clock select register 0 (TPS0) and the CKS0n1 bit of timer mode register $0 \cdot (TMR0nH)$. n: Channel number (n = 0 to 3))

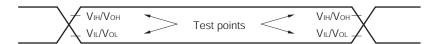
10

μs

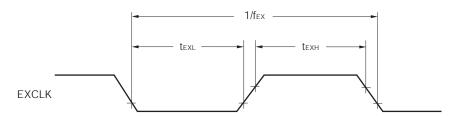
<R>> Minimum Instruction Execution Time during Main System Clock Operation



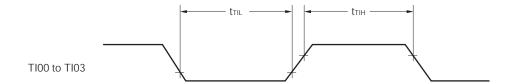
AC Timing Test Points

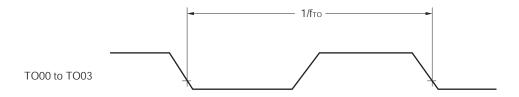


<R> External System Clock Timing

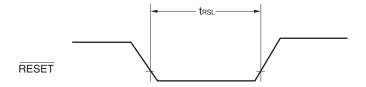


<R> TI/TO Timing



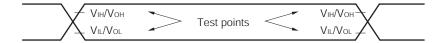


RESET Input Timing



2.5 Serial Interface Characteristics

AC Timing Test Points



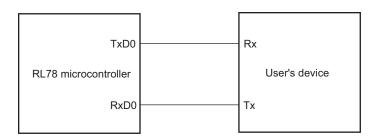
2.5.1 Serial array unit

(1) UART mode

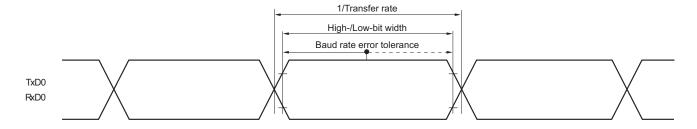
$(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.0 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate					fмск/6	bps
		Theoretical value of the maximum transfer rate fclk = fMCK = 20 MHz			3.3	Mbps

UART mode connection diagram



UART mode bit width (reference)



Remark fmck: Serial array unit operation clock frequency

(Operation clock to be set by the serial clock select register 0 (SPS0) and the CKS0n bit of the serial mode register 0nH (SMR0nH). n: Channel number (n = 0, 1))

(2) CSI mode (master mode, SCKp... internal clock output)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.0 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol		Conditions	MIN.	TYP.	MAX.	Unit
SCKp cycle time	tkcy1	tkcy1 ≥ 4/fclk	$2.7~V \leq V_{DD} \leq 5.5~V$	200			ns
			$2.0~V \leq V_{\text{DD}} \leq 5.5~V$	800			ns
SCKp high-/low-level width	tkh1, tkl1	2.7 V ≤ V _{DD} ≤ 5	$2.7~V \le V_{DD} \le 5.5~V$				ns
		$2.0~V \leq V_{DD} \leq 5.5~V$		tkcy1/2 - 50			ns
SIp setup time (to SCKp↑) Note 1	tsıĸı	2.7 V ≤ V _{DD} ≤ 5	.5 V	47			ns
		2.0 V ≤ V _{DD} ≤ 5	.5 V	110			ns
SIp hold time (from SCKp↑) Note 1	tksi1			19			ns
Delay time from SCKp↓ to SOp output Note 2	tkso1	C = 30 pF Note 3				25	ns

- **Notes 1.** When DAP0n = 0 and CKP0n = 0, or DAP0n = 1 and CKP0n = 1. The SIp setup time becomes "to SCKp↓" and SIp hold time becomes "from SCKp↓" when DAP0n = 0 and CKP0n = 1, or DAP0n = 1 and CKP0n = 0.
 - 2. When DAP0n = 0 and CKP0n = 0, or DAP0n = 1 and CKP0n = 1. The delay time to SOp output becomes "from SCKp↑" when DAP0n = 0 and CKP0n = 1, or DAP0n = 1 and CKP0n = 0.
 - 3. C is the load capacitance of the SCKp and SOp output lines.

(3) CSI mode (slave mode, SCKp... external clock input)

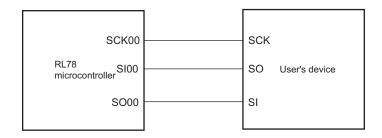
 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.0 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Co	ondition	S	MIN.	TYP.	MAX.	Unit
SCKp cycle time	tkcy2	$2.7~V \leq V_{DD} \leq 5.5$	V fi	лск > 16 MHz	8/fмск			ns
			fn	иск ≤ 16 MHz	6/fмск			ns
		$2.0~V \leq V_{DD} \leq 5.5$	5 V		6/ƒмск			ns
SCKp high-/low-level width	t _{KH2} ,	$2.0~V \leq V_{DD} \leq 5.5$	5 V		tkcy2/2			ns
	t _{KL2}							
SIp setup time (to SCKp [↑]) ^{Note 1}	tsık2	$2.7~\text{V} \leq \text{V}_{\text{DD}} \leq 5.5~\text{V}$		1/fмcк+ 20			ns	
		$2.0~V \le V_{DD} \le 5.5$	5 V		1/fмcк+ 30			ns
Slp hold time (from SCKp [↑]) Note 1	tksi2	2.0 V ≤ V _{DD} ≤ 5.5	5 V		1/fмcк+ 31			ns
Delay time from SCKp↓ to SOp	tks02	C = 30 pF Note 3	2.7 V s	$\leq V_{DD} \leq 5.5 \text{ V}$			2/fmck+50	ns
output Note 2			2.0 V s	$\leq V_{DD} \leq 5.5 \text{ V}$			2/fmck+ 110	ns

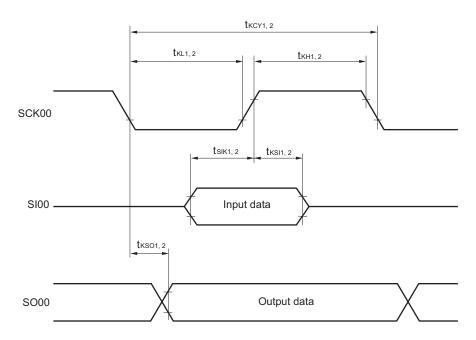
- Notes 1. When DAP0n = 0 and CKP0n = 0, or DAP0n = 1 and CKP0n = 1. The SIp setup time becomes "to SCKp↓" and the SIp hold time becomes "from SCKp↓" when DAP0n = 0 and CKP0n = 1, or DAP0n = 1 and CKP0n = 0.
 - 2. When DAP0n = 0 and CKP0n = 0, or DAP0n = 1 and CKP0n = 1. The delay time to SOp output becomes "from SCKp↑" when DAP0n = 0 and CKP0n = 1, or DAP0n = 1 and CKP0n = 0.
 - **3.** C is the load capacitance of the SOp output lines.
- **Remarks 1.** p: CSI number (p = 00, 01), n: Channel number (n = 0, 1)
 - 2. fmck: Serial array unit operation clock frequency (Operation clock to be set by the serial clock select register 0 (SPS0) and the CKS0n bit of the serial mode register 0nH (SMR0nH). n: Channel number (n = 0, 1))



CSI mode connection diagram



CSI mode serial transfer timing $(When \ DAP0n = 0 \ and \ CKP0n = 0, \ or \ DAP0n = 1 \ and \ CKP0n = 1.)$



Remark p: CSI number (p = 00, 01), n: Channel number (n = 0, 1)

(4) Simplified I²C mode

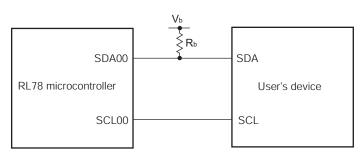
 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.0 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{ Vss} = 0 \text{ V})$

1111 10 10 100 0, 210 1 2 122 2 010 1, 100 0	· /				
Parameter	Symbol	Conditions	MIN.	MAX.	Unit
SCLr clock frequency	fscL	$C_b = 100 \text{ pF}, R_b = 3 \text{ k}\Omega$		400 Note 1	kHz
Hold time when SCLr = "L"	tLOW	$C_b = 100 \text{ pF}, R_b = 3 \text{ k}\Omega$	1150		ns
Hold time when SCLr = "H"	tніgн	$C_b = 100 \text{ pF}, R_b = 3 \text{ k}\Omega$	1150		ns
Data setup time (reception)	tsu: dat	$C_b = 100 \; pF, \; R_b = 3 \; k\Omega$	1/fMCK + 145 Note 2		ns
Data hold time (transmission)	thd: dat	$C_b = 100 \text{ pF}, R_b = 3 \text{ k}\Omega$	0	355	ns

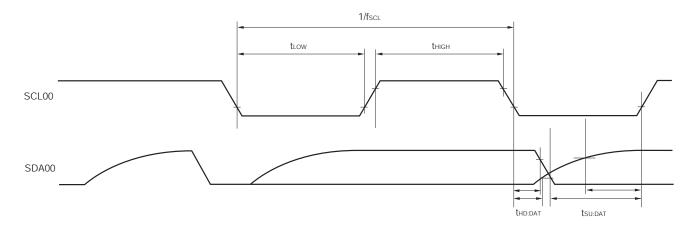
- Notes 1. The value must also be equal to or less than fmck/4.
 - 2. Set the fmck value to keep the hold time of SCLr = "L" and SCLr = "H".

Caution Select the N-ch open drain output (VDD tolerance) mode for the SDAr pin by using the port output mode register 0 (POM0).

Simplified I²C mode connection diagram



Simplified I2C mode serial transfer timing



- **Remarks 1.** R_b [Ω]: Communication line (SDAr) pull-up resistance, C_b [F]: Communication line (SCLr, SDAr) load capacitance
 - 2. r: IIC number (r = 00)
 - 3. fmck: Serial array unit operation clock frequency (Operation clock to be set by the serial clock select register 0 (SPS0) and the CKS0n bit of the serial mode register 0nH (SMR0nH). n: Channel number (n = 0))

<R> 2.5.2 Serial interface IICA

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.0 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

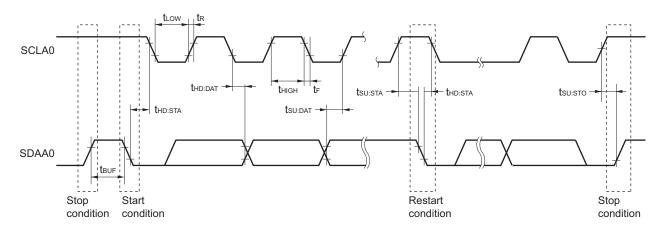
Parameter	Symbol	Conditions	Standa	rd Mode	Fast	Mode	Unit
			MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	fscL	Fast mode: fcLK ≥ 3.5 MHz			0	400	kHz
		Standard mode: fclk ≥ 1 MHz	0	100			kHz
Setup time of restart condition	tsu:sta		4.7		0.6		μS
Hold time ^{Note 1}	thd:sta		4.0		0.6		μS
Hold time when SCLA0 = "L"	tLOW		4.7		1.3		μS
Hold time when SCLA0 = "H"	tніgн		4.0		0.6		μS
Data setup time (reception)	tsu:dat		250		100		ns
Data hold time (transmission) ^{Note 2}	thd:dat		0	3.45	0	0.9	μS
Setup time of stop condition	tsu:sto		4.0		0.6		μS
Bus-free time	tBUF		4.7		1.3		μS

- Notes 1. The first clock pulse is generated after this period when the start/restart condition is detected.
 - 2. The maximum value (MAX.) of thD:DAT is during normal transfer and a wait state is inserted in the \overline{ACK} (acknowledge) timing.

Remark The maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at that time in each mode are as follows.

 $\label{eq:cb} \begin{aligned} \text{Standard mode:} \quad & C_b = 400 \text{ pF}, \ R_b = 2.7 \ k\Omega \\ \text{Fast mode:} \quad & C_b = 200 \text{ pF}, \ R_b = 1.7 \ k\Omega \end{aligned}$

IICA serial transfer timing



2.6 Analog Characteristics

<R> 2.6.1 A/D converter characteristics

(Target pin: ANI0 to ANI6, internal reference voltage)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.4 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	C	Conditions	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error ^{Notes 1, 2, 3}	AINL	10-bit resolution	V _{DD} = 5 V		±1.7	±3.1	LSB
			V _{DD} = 3 V		±2.3	±4.5	LSB
Conversion time	tconv	10-bit resolution	$2.7~V \leq V_{DD} \leq 5.5~V$	3.4		18.4	μs
		Target pin: ANI0 to ANI6	$2.4~V \leq V_{\text{DD}} \leq 5.5~V^{\text{ Note 5}}$	4.6		18.4	μs
		10-bit resolution Target pin: internal reference voltage Note 6	$2.4~V \leq V_{DD} \leq 5.5~V$	4.6		18.4	μs
Zero-scale error ^{Notes 1, 2, 3, 4}	Ezs	10-bit resolution	V _{DD} = 5 V			±0.19	%FSR
			V _{DD} = 3 V			±0.39	%FSR
Full-scale error ^{Notes 1, 2, 3, 4}	EFS	10-bit resolution	V _{DD} = 5 V			±0.29	%FSR
			V _{DD} = 3 V			±0.42	%FSR
Integral linearity error ^{Notes 1, 2, 3}	ILE	10-bit resolution	V _{DD} = 5 V			±1.8	LSB
			V _{DD} = 3 V			±1.7	LSB
Differential linearity error	DLE	10-bit resolution	V _{DD} = 5 V			±1.4	LSB
Notes 1, 2, 3			V _{DD} = 3 V			±1.5	LSB
Analog input voltage	VAIN	Target pin: ANI0 to	ANI6	0		V _{DD}	٧
		Target pin: internal	reference voltage Note 6		VREG Note 7		V

- **Notes 1.** TYP. Value is the average value at $T_A = 25$ °C. MAX. value is the average value $\pm 3\sigma$ at normal distribution.
 - 2. These values are the results of characteristic evaluation and are not checked for shipment.
 - 3. Excludes quantization error ($\pm 1/2$ LSB).
 - 4. This value is indicated as a ratio (%FSR) to the full-scale value.
 - 5. Set the LV0 bit in the A/D converter mode register 0 (ADM0) to 0 when conversion is done in the operating voltage range of 2.4 V ≤ V_{DD} < 2.7 V.
 - **6.** Set the LV0 bit in the A/D converter mode register 0 (ADM0) to 0 when the internal reference voltage is selected as the target for conversion.
 - 7. Refer to 2.6.3 Internal reference voltage characteristics.
 - Cautions 1. Arrange wiring and insert the capacitor so that no noise appears on the power supply/ground line.
 - 2. Do not allow any pulses that rapidly change such as digital signals to be input/output to/from the pins adjacent to the conversion pin during A/D conversion.
 - 3. Note that the internal reference voltage cannot be used as the reference voltage of the comparator when the internal reference voltage is selected as the target for A/D conversion.

<R>> 2.6.2 Comparator characteristics

$(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.0 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{ Vss} = 0 \text{ V})$

Parameter	Symbol	Conc	litions	MIN.	TYP.	MAX.	Unit
Input voltage range	IVREF	IVREF0 pin input (w	REF0 pin input (when C0VFR bit = 0)			VDD - 1.4	V
		Internal reference vo	ernal reference voltage (when C0VRF = 1) Note 1		VREG Note 2		٧
	IVCMP	IVCMP0 pin input	-0.3		VDD + 0.3	V	
Output delay	t d	VDD = 3.0 V,	High-speed mode			0.5	μs
		input slew rate > 50 mV/µs	Low-speed mode		2.0		μs
Operation stabilization wait time	tcmp			100			μs

Notes 1. When the internal reference voltage is selected as the reference voltage of the comparator, the internal reference voltage cannot be used as the target for A/D conversion.

2. Refer to 2.6.3 Internal reference voltage characteristics.

<R>> 2.6.3 Internal reference voltage characteristics

$(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.0 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Internal reference voltage	VREG		0.74	0.815	0.89	V
Operation stabilization wait time	tамр	When A/D converter is used (ADS register = 07H)	5			μs

Note The internal reference voltage cannot be simultaneously used by the A/D converter and the comparator; only one of them must be selected.

2.6.4 SPOR Circuit characteristics

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, \text{Vss} = 0 \text{ V})$

Para	ameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection	Power supply	V _{SPOR0}	Power supply rise time	4.08	4.28	4.45	٧
voltage	voltage level		Power supply fall time	4.00	4.20	4.37	٧
		VSPOR1	Power supply rise time	2.76	2.90	3.02	٧
			Power supply fall time	2.70	2.84	2.96	V
		VSPOR2	Power supply rise time	2.44	2.57	2.68	V
			Power supply fall time	2.40	2.52	2.62	٧
		V _{SPOR3}	Power supply rise time	2.05	2.16	2.25	٧
			Power supply fall time	2.00	2.11	2.20	٧
Minimum pulse	Minimum pulse width Note TLSPW 300			μs			

Note Time required for the reset operation by the SPOR when VDD becomes under VSPOR.

<R> Caution Set the detection voltage (Vspor) in the operating voltage range. The operating voltage range depends on the setting of the user option byte (000C2H). The operating voltage range is as follows:

When the CPU operating frequency is from 1 MHz to 20 MHz: V_{DD} = 2.7 to 5.5 V When the CPU operating frequency is from 1 MHz to 5 MHz: V_{DD} = 2.0 to 5.5 V

2.6.5 Power supply voltage rising slope characteristics

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, \text{ Vss} = 0 \text{ V})$

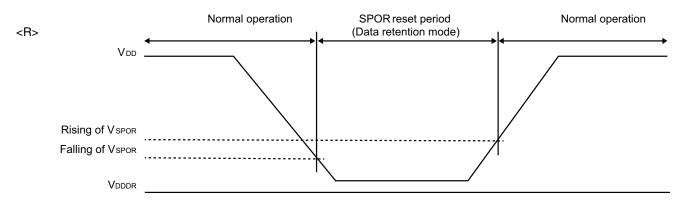
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Power supply voltage rising slope	SVDD				54	V/ms

2.6.6 Data retention power supply voltage characteristics

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, \text{ Vss} = 0 \text{ V})$

10 10 100 0, 100 0 1						
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention power supply voltage	VDDDR		1.9		5.5	V

Caution Data in the RESF register is retained until the power supply voltage becomes under the minimum value of the data retention power supply voltage (VDDDR). Note that data in the RESF register might not be cleared even if the power supply voltage becomes under the minimum value of the data retention power supply voltage (VDDDR).



2.7 Flash Memory Programming Characteristics

$(T_A = 0 \text{ to } + 40^{\circ}\text{C}, 4.5 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Code flash memory rewritable times Notes 1, 2, 3	Cerwr	Retained for 20 years.	T _A = +85°C	1000			Times

- **Notes 1.** 1 erase + 1 write after the erase is regarded as 1 rewrite. The retaining years are until next rewrite after the rewrite.
 - **2.** When using flash memory programmer.
 - **3.** These are the characteristics of the flash memory and the results obtained from reliability testing by Renesas Electronics Corporation.

2.8 Dedicated Flash Memory Programmer Communication (UART)

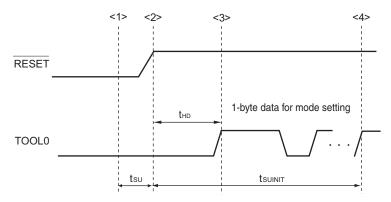
$(T_A = 0 \text{ to } + 40^{\circ}\text{C}, 4.5 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate				115,200		bps

Remark The transfer rate during flash memory programming is fixed to 115,200 bps.

2.9 Timing of Entry to Flash Memory Programming Modes	2.9	Timing of	of Entry to	Flash	Memory	Programming	Modes
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Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Time to complete the communication for the initial setting after the external reset is released	tsuinit	SPOR reset must be released before the external reset is released.			100	ms
Time to release the external reset after the TOOL0 pin is set to the low level	tsu	SPOR reset must be released before the external reset is released.	10			μs
Time to hold the TOOL0 pin at the low level after the external reset is released	tно	SPOR reset must be released before the external reset is released.	1			ms



- <1> The low level is input to the TOOL0 pin.
- <2> The external reset is released (SPOR reset must be released before the external reset is released.).
- <3> The TOOL0 pin is set to the high level.
- <4> Setting of entry to the flash memory programming mode by UART reception is completed.

Remark tsuinit: Communication for the initial setting must be completed within 100 ms after the external reset is released during this period.

tsu: Time to release the external reset after the TOOL0 pin is set to the low level

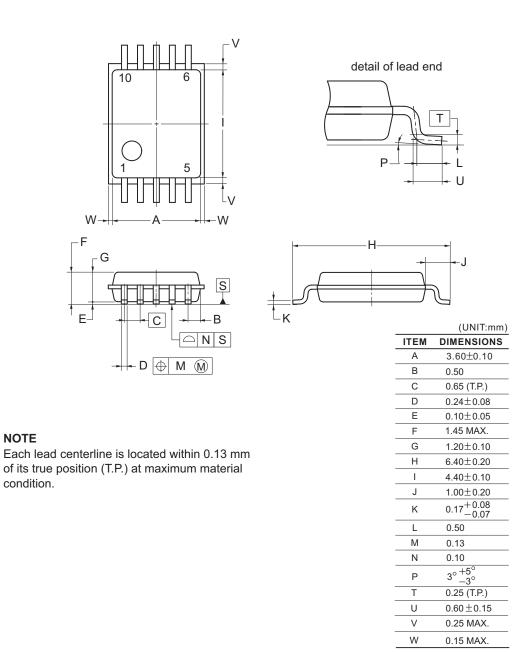
thd: Time to hold the TOOL0 pin at the low level after the external reset is released

3. PACKAGE DRAWINGS

3.1 10-pin products

<R> R5F10Y17ASP, R5F10Y16ASP, R5F10Y14ASP

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LSSOP10-4.4x3.6-0.65	PLSP0010JA-A	P10MA-65-CAC-2	0.05



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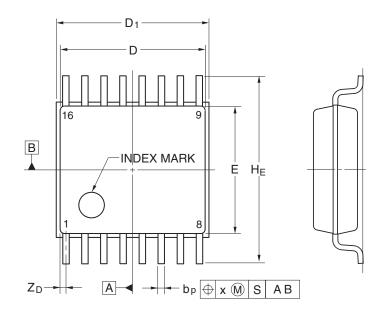
NOTE

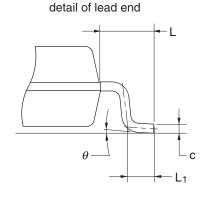
3.2 16-pin products

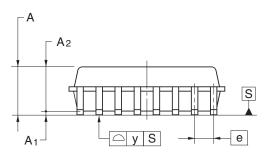
R5F10Y47ASP, R5F10Y46ASP, R5F10Y44ASP

<R>

JEITA Package code	RENESAS code	Previous code	MASS(TYP.)[g]
P-SSOP16-4.4x5-0.65	PRSP0016JC-B	P16MA-65-FAB	0.08

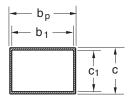






Dimension in Millimeters Referance Symbol Nom Min Max D 4.85 5.00 5.15 5.20 D_1 5.05 5.35 Е 4.40 4.20 4.60 A_2 1.50 A_1 0.075 0.125 0.175 1.725 Α 0.17 0.24 0.32 b_p 0.22 b₁ 0.17 0.20 0.14 c₁ 0.15 8° θ 0° H_E 6.40 6.20 6.60 е 0.65 Х 0.13 у 0.10 $Z_{\text{\scriptsize D}}$ 0.225 L 0.35 0.65 0.50 L_1 1.00

Terminal cross section



RL78/G10 Datasheet

			Description
Rev.	Date	Page	Summary
1.00	Apr 15, 2013	-	First Edition issued
2.00	Jan 10, 2014	1, 2	Modification of descriptions in 1.1 Features
		3	Modification of description in 1.2 List of Part Numbers
		4	Modification of remark 2 in 1.3.1 10-pin products and 1.3.2 16-pin products
		8, 9	Addition of description of R5F10Y17ASP in 1.6 Outline of Functions
		11	Modification of description in 2.1 Absolute Maximum Ratings
		12	Modification of description in 2.2 Oscillator Characteristics
		13, 14	Modification of description, notes 1 to 4, and caution in 2.3.1 Pin characteristics
		16	Addition of description, notes 1 to 6, and remarks 1 and 2 in (2) Flash ROM: 4 KB of 10-pin products, and 16-pin products
		17	Addition of description, notes 1 to 6, and remarks 1 to 3 in (3) Peripheral Functions (Common to all products)
		18	Modification of description in 2.4 AC Characteristics
		19	Addition of figure of Minimum Instruction Execution Time during Main System Clock Operation
		19	Addition of figure of External System Clock Timing
		20	Modification of TI/TO Timing
		25	Addition of description in 2.5.2 Serial interface IICA
		26	Modification of description and notes 1 to 6 in 2.6.1 A/D converter characteristics
		27	Addition of description, notes 1 and 2 in 2.6.2 Comparator characteristics
		27	Addition of description and note in 2.6.3 Internal reference voltage characteristics
		28	Additioni of caution in 2.6.4 SPOR Circuit characteristics
		28	Addition of figure in 2.6.6 Data retention power supply voltage characteristics
		31	Addition of R5F10Y17ASP in 3.1 10-pin products
		32	Modification of package drawing in 3.2 16-pin products

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NOTES FOR CMOS DEVICES

- (1) VOLTAGE APPLICATION WAVEFORM AT INPUT PIN: Waveform distortion due to input noise or a reflected wave may cause malfunction. If the input of the CMOS device stays in the area between VIL (MAX) and VIH (MIN) due to noise, etc., the device may malfunction. Take care to prevent chattering noise from entering the device when the input level is fixed, and also in the transition period when the input level passes through the area between VIL (MAX) and VIH (MIN).
- (2) HANDLING OF UNUSED INPUT PINS: Unconnected CMOS device inputs can be cause of malfunction. If an input pin is unconnected, it is possible that an internal input level may be generated due to noise, etc., causing malfunction. CMOS devices behave differently than Bipolar or NMOS devices. Input levels of CMOS devices must be fixed high or low by using pull-up or pull-down circuitry. Each unused pin should be connected to VDD or GND via a resistor if there is a possibility that it will be an output pin. All handling related to unused pins must be judged separately for each device and according to related specifications governing the device.
- (3) PRECAUTION AGAINST ESD: A strong electric field, when exposed to a MOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it when it has occurred. Environmental control must be adequate. When it is dry, a humidifier should be used. It is recommended to avoid using insulators that easily build up static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work benches and floors should be grounded. The operator should be grounded using a wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions need to be taken for PW boards with mounted semiconductor devices.
- (4) STATUS BEFORE INITIALIZATION: Power-on does not necessarily define the initial status of a MOS device. Immediately after the power source is turned ON, devices with reset functions have not yet been initialized. Hence, power-on does not guarantee output pin levels, I/O settings or contents of registers. A device is not initialized until the reset signal is received. A reset operation must be executed immediately after power-on for devices with reset functions.
- (5) POWER ON/OFF SEQUENCE: In the case of a device that uses different power supplies for the internal operation and external interface, as a rule, switch on the external power supply after switching on the internal power supply. When switching the power supply off, as a rule, switch off the external power supply and then the internal power supply. Use of the reverse power on/off sequences may result in the application of an overvoltage to the internal elements of the device, causing malfunction and degradation of internal elements due to the passage of an abnormal current. The correct power on/off sequence must be judged separately for each device and according to related specifications governing the device.
- (6) INPUT OF SIGNAL DURING POWER OFF STATE: Do not input signals or an I/O pull-up power supply while the device is not powered. The current injection that results from input of such a signal or I/O pull-up power supply may cause malfunction and the abnormal current that passes in the device at this time may cause degradation of internal elements. Input of signals during the power off state must be judged separately for each device and according to related specifications governing the device.

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